

Supporting information for

Nonlithographic Fabrication of Crystalline Silicon Nanodots on Graphene

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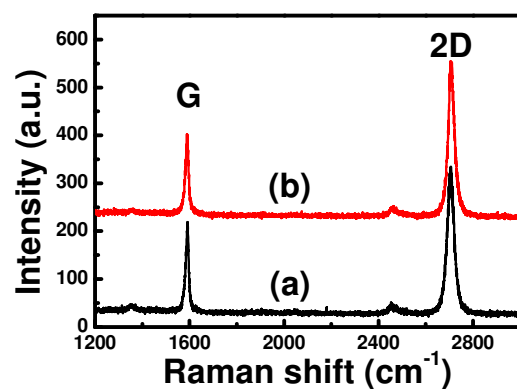


Figure S1. Raman spectra of the monolayer graphene samples (a) before and (b) after annealing at 400 °C.

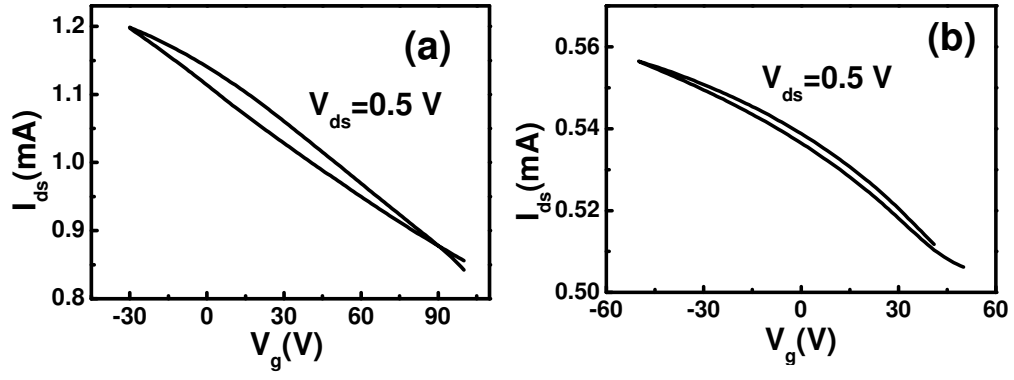


Figure S2. I_{ds} - V_g characteristics of monolayer graphene and graphene decorated with Si nanodots before annealing in pure N_2 environment.